

CMPT918

NPN SILICON RF TRANSISTOR



SOT-23 CASE

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPT918 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high frequency (VHF/UHF) amplifier and oscillator applications.

**Marking code is C3B.**

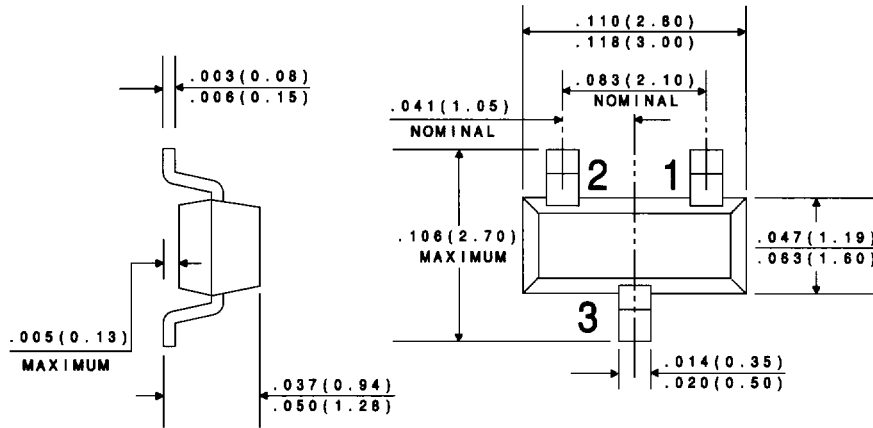
**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	15	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current	$I_C$	50	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^{\circ}\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=15\text{V}$		10	nA
$BV_{CBO}$	$I_C=1.0\mu\text{A}$	30		V
$BV_{CEO}$	$I_C=3.0\text{mA}$	15		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	3.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.4	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.0	V
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=3.0\text{mA}$	20		
$f_T$	$V_{CE}=10\text{V}, I_C=4.0\text{mA}, f=100\text{MHz}$	600		MHz
$C_{ob}$	$V_{CB}=0\text{V}, I_E=0, f=1.0\text{MHz}$		3.0	pF
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		1.7	pF
$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		2.0	pF
$P_{out}$	$V_{CB}=15\text{V}, I_C=8.0\text{mA}, f=500\text{MHz}$	30		mW
$G_{pe}$	$V_{CB}=12\text{V}, I_C=6.0\text{mA}, f=200\text{MHz}$	11		dB
NF	$V_{CE}=6.0\text{V}, I_C=1.0\text{mA}, R_S=50\Omega, f=60\text{MHz}$		6.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

DATA SHEET

R2